Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	148	liang near mong-song.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:36
L2	7	1 and (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:37
L3	47	lu near yung-cheng.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:37
L4	39	3 and (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:39
L5	0	chang near huilin.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:40
L6	2935	438/624.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:41
L7	546	(low near dielectric) near45 (treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:41
L8	522	(low near dielectric) near25 (treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:42
L9	22	(low near dielectric) near25 (second near5 treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:42

L10	8	9 and stability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:45
L11	112	7 and stability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:52
L12	8	7 and (mechanical near stability)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 17:46
L13	19	7 and (temperature near25 stability)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:03
L14	81315	(second near5 treat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:03
L15	38282	(second near2 treat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:03
L16	17576	(second near treat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:04
L17	2	(second near treat$4) near15 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:04
L18	18	(second near3 treat$4) near25 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:16
L19	420	(hydrogen near3 plasma) near15 (microwave)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:18

L20	3	(hydrogen near3 plasma) near15 (microwave) near15 (electron near beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:17
L21	24	(hydrogen near3 plasma) near15 (microwave) near25 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:18
L22	24	(hydrogen near3 plasma) near15 (microwave) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:23
L23	6	(hydrogen near3 plasma) near15 (electron near beam) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:41
L24	6	(hydrogen near3 plasma) near15 (ultraviolet near radiation) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:32
L25	10	(high near temperature) near15 (ultraviolet near radiation) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:33
L26	0	(carbon near3 plasma) near15 (electron near beam) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:40
L27	4	(carbon near3 plasma) near15 (high near temperature) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:40
L28	16	(hydrogen near3 plasma) near15 (high near temperature) near15 (treatments)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:45
L29	2	(first near3 treatment) near15 (pores) near15 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:47

L30	4	(second near3 treatment) near15 (pores) near15 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 18:59
L31	49215	(first near3 treatment) (hydrogen near2 plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:00
L32	1669	((first near3 treatment) (hydrogen near2 plasma)) near10 (low ear4 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:00
L33	102	((first near3 treatment) (hydrogen near2 plasma)) near10 (low near4 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:00
L34	52	((first near3 treatment) (hydrogen near2 plasma)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:01
L35	0	((first near3 treatment) near15 (hydrogen near2 plasma)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:01
L36	0	((first near3 treatment) near15 (hydrogen near2 plasma)) near10 (low3 near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:06
L37	0	((treatment) near15 (hydrogen near2 plasma)) near10 (low3 near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:01
L38	21	((treatment) near15 (hydrogen near2 plasma)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:01
L39	20	((treatment) near5 (hydrogen near2 plasma)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:02

L40	0	((treatment) near5 (microwave near5 hydrogen near2 plasma)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:02
L41	0	((first near3 treatment) near15 (high near temperature)) near10 (low3 near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:06
L42	0	((first near3 treatment) near15 (high near temperature)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:06
L43	0	((first near3 treatment) near25 (high near temperature)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:06
L44	35	((treatment) near25 (high near temperature)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:07
L45	31	((treatment) near5 (high near temperature)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:10
L46	0	((second near treatment) near5 (high near temperature)) near10 (low near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 19:10

	U	1	Document ID	Title
1			US 20040234779 A1	Fluorinated aromatic precursors
2			US 20030181537 A1	Process for producing dielectric layers by using multifunctional carbosilanes
3			US 20030157311 A1	Mesoporous films having reduced dielectric constants
4			US 20020132061 A1	Method for producing a porous coating
5			US 6818289 B2	Mesoporous films having reduced dielectric constants

	Current OR	Pages	Issue Date	Current XRef
6	428/447	28	20031216	257/E21.259; 257/E21.26; 257/E21.261; 257/E21.264; 427/489; 427/515; 428/450
7	428/304.4	18	20030715	106/14.13; 106/14.41; 257/E21.273; 427/255.11; 427/372.2; 427/376.2; 427/419.2; 428/312.2
8	118/724	37	20000711	118/715; 118/723ER; 118/723MR; 118/726; 257/E21.259